a. Anut Keima

JAYPEE UNIVERSITY OF INFORMATION TECHNOLOGY, WAKNAGHAT **TEST -2 EXAMINATIONS-2022**

B.Tech-VI Semester (ECE)

COURSE CODE: 18B11EC612

MAX. MARKS: 25

COURSE NAME: VLSI Technology

COURSE CREDITS: 04

MAX. TIME: 1 Hour 30 Min

Note: All questions are compulsory. Marks are indicated against each question in square brackets.

Q1.	Write short notes	on any two	of the	followings:
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[2x2.5]

- MOSFET Scaling
- Subthreshold Conduction b.
- Velocity Saturation
- Q2. Develop the formula of V_{IH} in case of resistive load inverter.

- [4]
- Q3. What do you understand about noise margins NM_H and NM_L ? Explain in detail. Q4. Explain the voltage transfer curve of the MOS inverter. Also mention the labels.

[4] [4]

Q5. Describe oxide related capacitances in MOSFETs.

[4]

Q6. Consider the MOS inverter with $V_{DD}=5V$, $k_n'=30\mu\text{A/V}^2$, and $V_{T0}=1V$, designed with resistive load with R_L =205K Ω and V_{OL} =0.2V. Find the value of the aspect ratio (W/L) of the driver transistor. [4]